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STATEMENT BY APPLICANT**

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|----------------------|---------------------|
| Application Number   | 09/944985           |
| Filing Date          | August 30, 2001     |
| First Named Inventor | Bhattacharyya, Arup |
| Group Art Unit       | Unknown             |
| Examiner Name        | Unknown             |

Sheet 1 of 1

Attorney Docket No: 01303.023US1

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| Examiner Initials* | USP Document Number | Publication Date | Name of Patentee or Applicant of cited Document | Class | Subclass | Filing Date If Appropriate |
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| Examiner Initials* | Foreign Document No | Publication Date | Name of Patentee or Applicant of cited Document | Class | Subclass | T <sup>2</sup> |
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|                    |                     |                  |   |       |          |                |

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

| Examiner Initials* | Cite No <sup>1</sup> | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T <sup>2</sup> |
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